

Duration: 3hrs

Max. Marks:80

NB:

- (1) Question No.1 is compulsory.
- (2) Answer any **three** from remaining questions.
- (3) **Figures** to the right indicate full marks.
- (4) Assume suitable data if required.

**Q.1** Attempt **any four**

- a Compare JFET and MOSFET 5
- b Explain the Significance of stability factor 5
- c Why crystal oscillator is most stable oscillator? 5
- d Describe thermal runaway in BJT 5
- e What is clipping and clamping explain with one example. 5

**Q.2**

- a Draw BJT CE amplifier with any biasing circuit and derive expression for voltage gain, input impedance and output impedance. 10
- b What is Varactor diode? Explain construction and operation of varactor diode. 10

**Q.3**

- a Sketch the circuit of Wein Bridge Oscillator using BJT and derive an expression for the frequency of oscillation. 10
- b For Common source amplifier with N-channel EOMOSFET determine  $A_v$ ,  $Z_i$ , and  $Z_o$ . 10  
 $V_{DD}=21V, R_1=42K, R_2=33K, R_D=5K, R_S=1.5K$ . The MOSFET parameters are:  
 $V_{TN}=1.5V, K_n=0.5mA/V^2$

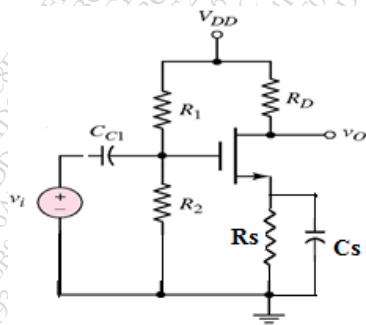


Fig.2

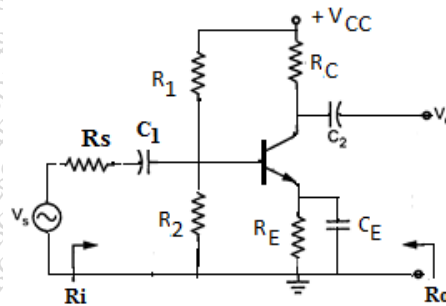


Fig.3

**Q.4** For the amplifier shown in Fig.3 analyze and determine. Derive the expression for small- 10

- a signal voltage gain, input and output impedance. BJT and circuit parameters are:  
 $\beta = 100, V_{BE} = 0.7V, V_A = 100V, R_1=93.7K, R_2=6.3k, R_C=6K, R_S=0.5K, V_{CC}=12V$ . 10
- b Draw the constructional diagram of N-Channel JFET, and explain the operation and thus obtain the V-I characteristics. 10

Q.5

- a) An N-Channel FET with common drain amplifier shown in fig.4 has the following parameters:  $I_{DSS}=10\text{mA}$ , at  $V_P=-4\text{V}$ . Determine Small signal voltage gain, input impedance and output impedance. If  $R_1=10\text{M}$ ,  $R_2=2\text{M}$ ,  $V_{DD}=18\text{V}$ ,  $R_S=1.2\text{k}$ ,  $R_L=10\text{K}$ . 10

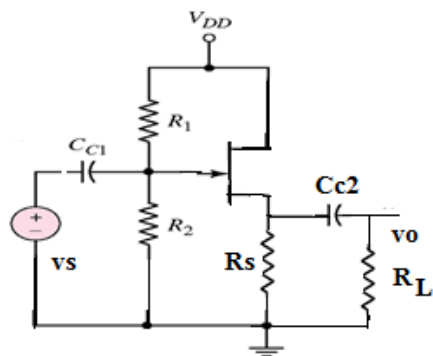


Fig.4

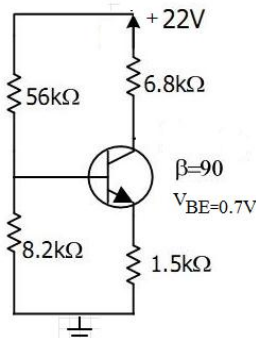


Fig.5

- b) For the circuit shown in figure 5. Determine Q point co-ordinates. 10

Q.6

Attempt the following

- a) LC oscillator and its application. 5
- b) Small signal h- parameter parameters of BJT 5
- c) Depletion MOSFET operation. 5
- d) Compare BJT and FET 5

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